

CJ3400-HF (N-Channel)

Reverse Voltage: 30 Volts

Forward Current: 5.8 A

RoHS Device

Halogen Free



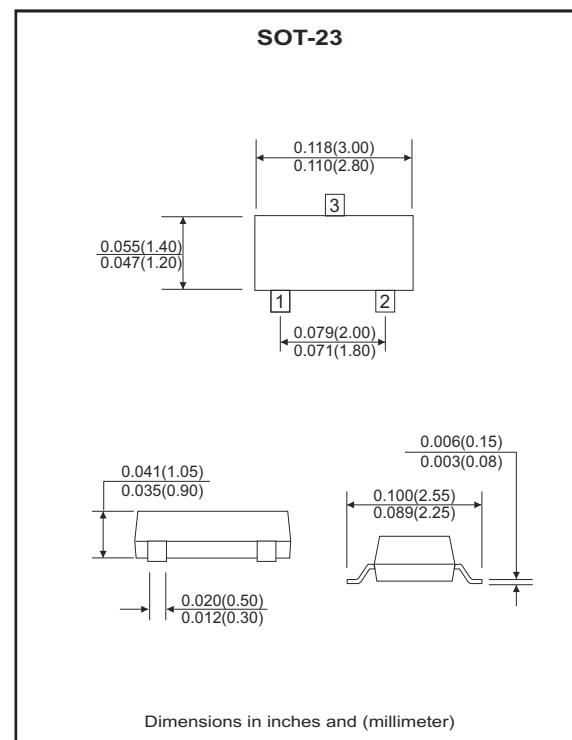
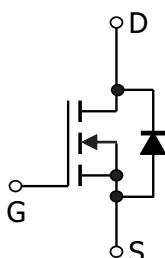
Features

- N-Channel Enhancement mode field effect transistor.
- High dense cell design for extremely low R_{DS(ON)}
- Exceptional on-resistance and maximum DC current capability.

Mechanical data

- Case: SOT-23, molded plastic.
- Terminals: solderable per MIL-STD-750, method 2026.

Circuit diagram



Maximum Ratings (Ta=25 °C unless otherwise noted)

Parameter	Symbol	Value	Units
Drain-source voltage	V _{DS}	30	V
Gate-source voltage	V _{GS}	±12	V
Continuous drain current	I _D	5.8	A
Drain current-pulsed (note 1)	I _{DM}	30	A
Power dissipation	P _D	350	mW
Thermal resistance from Junction to ambient (note 2)	R _{θJA}	357	°C/W
Junction temperature	T _J	150	°C
Storage temperature	T _{STG}	-55 to +150	°C

Electrical Characteristics (Ta=25 °C unless otherwise noted)

Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source breakdown voltage	V _{GS} =0V, I _D =250μA	V _{(BR)DSS}	30			V
Zero gate voltage drain current	V _{DS} =24V, V _{GS} =0V	I _{DSS}			1	μA
Gate-Source leakage current	V _{GS} =±12V, V _{DS} =0V	I _{GSS}			±100	nA
On Characteristics						
Static drain-source on-resistance (note 3)	V _{GS} =10V, I _D =5.8A	R _{DS(ON)}			35	mΩ
	V _{GS} =4.5V, I _D =5A				40	
	V _{GS} =2.5V, I _D =4A				52	
Forward transconductance	V _{DS} =5V, I _D =5A	g _{FS}	8			S
Gate threshold voltage	V _{DS} =V _{GS} , I _D =250μA	V _{GS(th)}	0.7		1.4	V
Dynamic Characteristics (note 3,4)						
Input capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	C _{iss}			1050	pF
Output capacitance		C _{oss}			99	
Reverse transfer capacitance		C _{rss}			77	
Gate resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	R _g			3.6	Ω
Switching Characteristics (note 3,4)						
Turn-on delay time	V _{GS} =10V, V _{DS} =15V, R _L =2.7Ω, R _{GEN} =3Ω	t _{d(on)}			5	ns
Turn-on rise time		t _r			7	
Turn-off delay time		t _{d(off)}			40	
Turn-off Fall time		t _f			6	
Drain-source diode characteristics and maximum ratings						
Diode forward voltage (note 3)	I _s =1A, V _{GS} =0V	V _{SD}			1	V

Note:

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface mounted on FR4 Board, t < 5sec.
3. Pulse test; Pulse width ≤300μs, Duty cycle ≤ 2%.
4. Guaranteed by design, not subject to production testing.

RATING AND CHARACTERISTIC CURVES (CJ3400-HF)

Fig.1- Output Characteristics

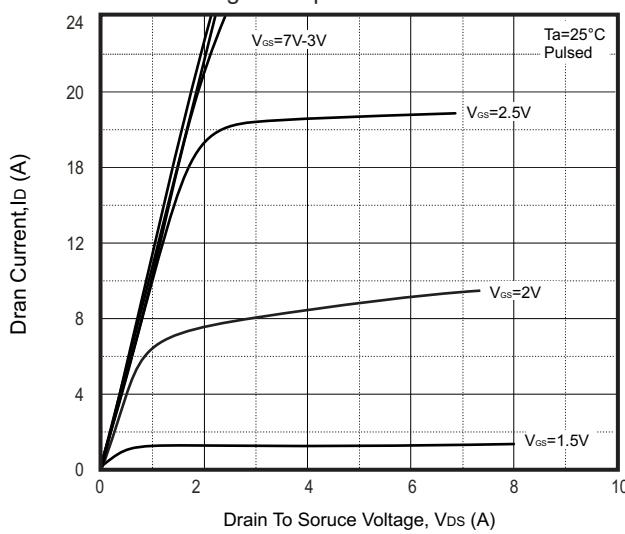


Fig.2- Transfer Characteristics

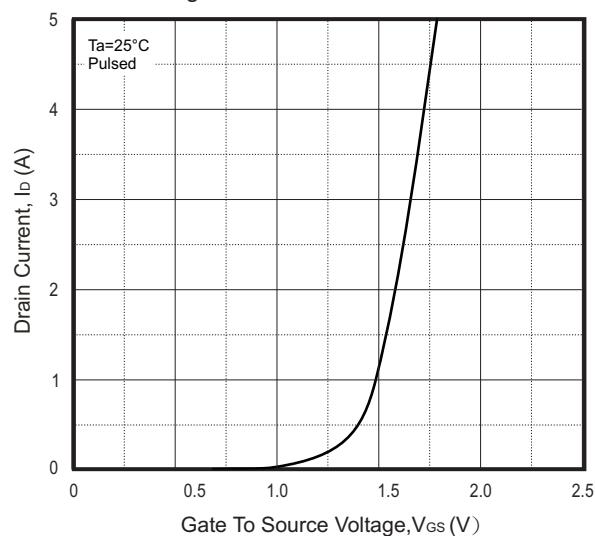


Fig.3 - $R_{DS(ON)} — I_D$

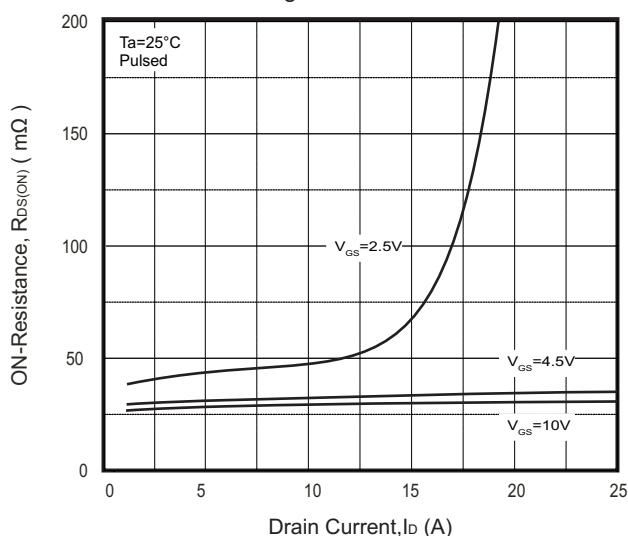


Fig.4- $R_{DS(ON)} — V_{GS}$

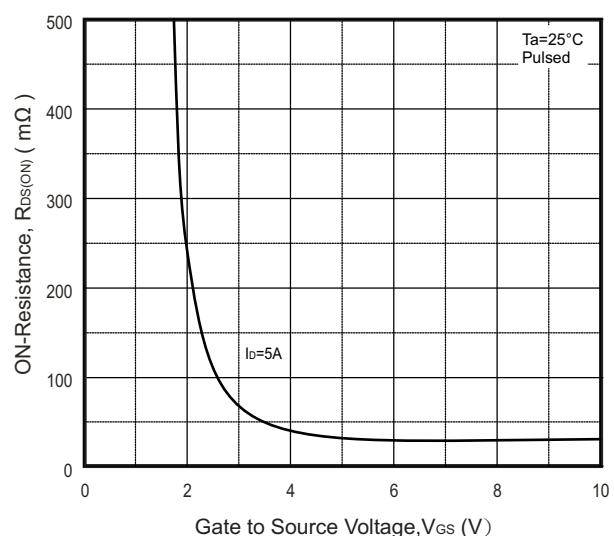
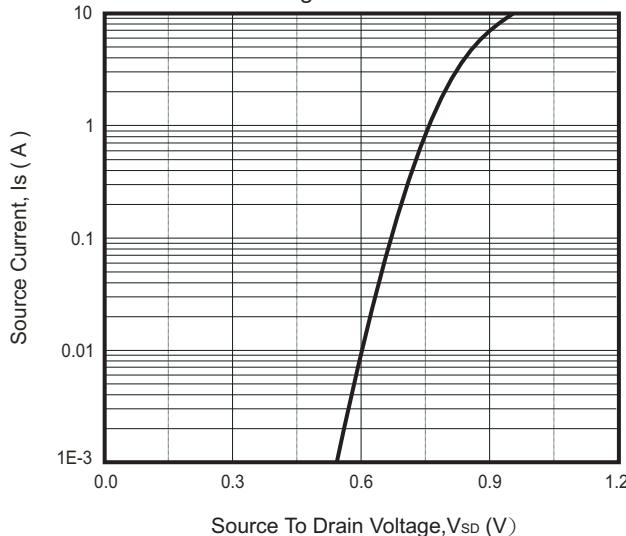


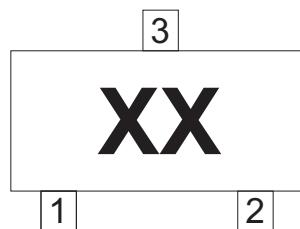
Fig.5 - $I_S — V_{SD}$



Company reserves the right to improve product design , functions and reliability without notice.

Marking Code

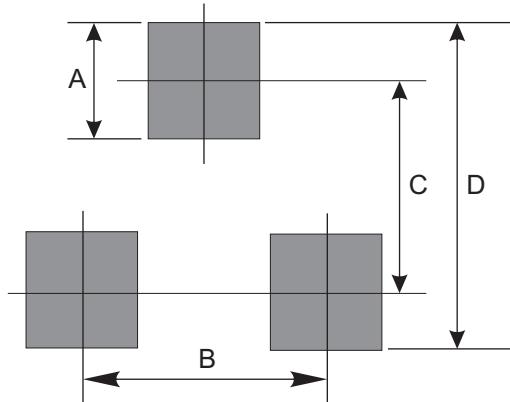
Part Number	Marking Code
CJ3400-HF	R0



xx = Product type marking code

Suggested PAD Layout

SIZE	SOT-23	
	(mm)	(inch)
A	0.80	0.031
B	1.90	0.075
C	2.02	0.080
D	2.82	0.111



Standard Packaging

Case Type	Qty Per Reel	Reel Size
	(Pcs)	(inch)
SOT-23	3,000	7